SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

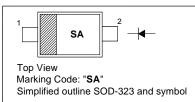
- Small surface mounting type
- Ultra low V_F
- High reliability

Applications

• High frequency rectification switching regulation

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	30	V
DC Reverse Voltage	V_R	20	V
Mean Rectifying Current	Io	0.5	А
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I _{FSM}	2	А
Junction Temperature	T _j	125	°C
Storage Temperature Range	Ts	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100 \text{ mA}$ at $I_F = 500 \text{ mA}$	V _F	0.36 0.47	>
Reverse Current at $V_R = 20 \text{ V}$	I _R	100	μΑ

Note: ESD sensitive product handling required.









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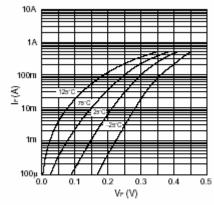


Fig.1 Forward characteristics

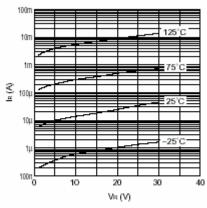


Fig.2 Reverse characteristics

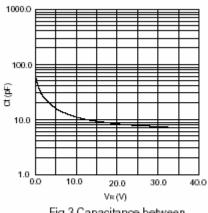


Fig.3 Capacitance between terminals characteristics

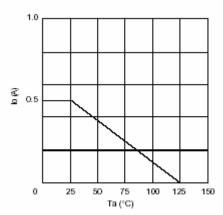


Fig.4 Derating curve













Dated: 01/09/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

